

OK to  
enter  
HCH  
6/7/05

**Amendments to the CLAIMS:**

Without prejudice, this listing of the claims replaces all prior versions and listings of the claims in the present application:

**LISTING OF CLAIMS:**

1-15. (Canceled).

16. (Currently Amended) A method for producing a semiconductor component having a semiconductor substrate, comprising the steps of:  
producing a first porous layer in the semiconductor component; and  
producing one of a hollow and a cavity in the semiconductor component ~~one of~~ under ~~and from~~ the first porous layer;  
wherein the one of the hollow and the cavity producing step includes the substep of producing a second porous layer having a porosity of more than approximately 70% under the first porous layer, and  
wherein the one of the hollow and the cavity is produced in the one of the hollow and the cavity producing step from the second porous layer by an annealing step ~~or by an etching step with a porosity of 100%~~.

17. (Previously Presented) The method according to claim 16, wherein the semiconductor component includes a multilayer semiconductor element.

18. (Previously Presented) The method according to claim 16, wherein the semiconductor component includes a micromechanical component.

19. (Previously Presented) The method according to claim 16, wherein the semiconductor component includes a pressure sensor.

20. (Previously Presented) The method according to claim 16, wherein the semiconductor substrate includes silicon.

21. (Canceled).

22. (Currently Amended) The method according to claim ~~[[21]]~~ 16, wherein the second porous layer has a porosity of approximately 85% to 95%.

23. (Canceled).